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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 1

Complete if Known	
Application Number	~~Not Yet Assigned~~ 10/659,134
Filing Date	~~Concurrently~~ SEPTEMBER 10, 2003
First Named Inventor	Mohammad R. Mirabedini
Art Unit	~~Not Yet Assigned~~ 2823
Examiner Name	~~Not Yet Assigned~~ COLEMAN
Attorney Docket Number	03-0730

OTHER PRIOR ART-NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
	1	Nobuyuki Sugii, Digh Hisamoto, Katsuyoshi Washio, Natsuki Yokoyama, and Shin'ichiro Kimura, "Enhanced Performance of Strained-Si MOSFETs on CMP SiGe Virtual Substrate," IEEE, 2001, 0-7803-7052-X/01, p. 1-4.	
	2	Paul Comita, AnnaLena Thilderkvist, and Arkadii V. Samoilov, "Applied Materials FEOL Seminar 2002," October 29, 2002, p. 1-37.	
	3	K. Rim, S. Koester, M. Hargrove, J. Chu, P. M. Mooney, J. Ott, T. Kanarsky, P. Ronsheim, M.leong, A. Grill, and H.-S. P. Wong, "Strained Si NMOSFETs for High Performance CMOS Technology," IEEE 2001 Symposium on VLSI Technology Digest of Technical Papers, 2001, p. 59 (1-2).	
	4	Yee-Chia Yeo, Qiang Lu, Chenming Hu, Tsu-Jae King, T. Kawashima, M. Oishi, S. Mashiro, and J. Sakai, "Enhanced performance in sub-100 nm CMOSFETs using strained epitaxial silicon-germanium", IEEE International Electron Device Meeting Technical Digest, pp. 753-756, San Francisco, CA, Dec. 2000, www.eecs.berkeley.edu/IPRO/Summary/01abstracts/ycyeo.1.html, p. 1-4.	
	5	R.E. Stallcup, A.F. Aviles, and J.M. Perez, "Atomic Resolution Ultrahigh Vacuum Scanning Tunneling Microscopy of Epitaxial Diamond (100) Films," Appl. Phys. Lett. 66 (18), American Institute of Physics, 1 May 1995, p. 2331-2333.	
	6	Akira Yamada, Tatsuro Watahiki, Shuhei Yagi, Katsuya Abe, and Makoto Konagai, "Epitaxial Growth of Strained $Si_{1-x}C_x$ on Si and Its Application to MOSFET," International Symposium on Quantum Effect Electronics, 2002.	

Examiner Signature		Date Considered	7/29/2005

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1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.